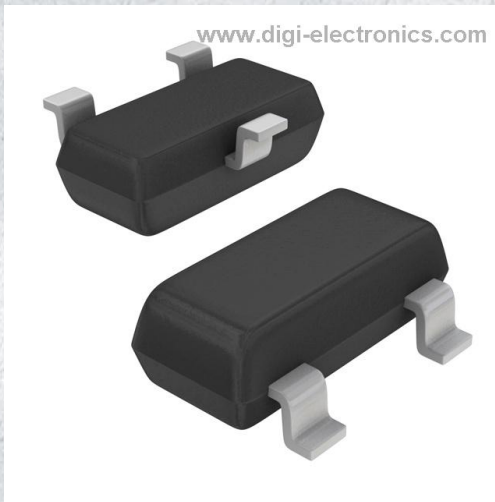


BZX84C4V3LT1G Datasheet



<https://www.DiGi-Electronics.com>

| | |
|------------------------------|---|
| DiGi Electronics Part Number | BZX84C4V3LT1G-DG |
| Manufacturer | onsemi |
| Manufacturer Product Number | BZX84C4V3LT1G |
| Description | DIODE ZENER 4.3V 250MW SOT23-3 |
| Detailed Description | Zener Diode 4.3 V 225 mW \pm 7% Surface Mount SOT-23-3 (TO-236) |

This model BZX84C4V3LT1G is available at DiGi Electronics.

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Purchase and inquiry

Manufacturer Product Number:

BZX84C4V3LT1G

Series:

BZX84CxxxLT1G

Voltage - Zener (Nom) (Vz):

4.3 V

Power - Max:

225 mW

Current - Reverse Leakage @ Vr:

3 μ A @ 1 V

Operating Temperature:

-65°C ~ 150°C (TJ)

Package / Case:

TO-236-3, SC-59, SOT-23-3

Base Product Number:

BZX84C4

Manufacturer:

onsemi

Product Status:

Active

Tolerance:

\pm 7%

Impedance (Max) (Zzt):

90 Ohms

Voltage - Forward (Vf) (Max) @ If:

900 mV @ 10 mA

Mounting Type:

Surface Mount

Supplier Device Package:

SOT-23-3 (TO-236)

Environmental & Export classification

RoHS Status:

ROHS3 Compliant

REACH Status:

REACH Unaffected

HTSUS:

8541.10.0050

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

Zener Voltage Regulators

250 mW SOT-23 Surface Mount

BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series

This series of Zener diodes is offered in the convenient, surface mount plastic SOT-23 package. These devices are designed to provide voltage regulation with minimum space requirement. They are well suited for applications such as cellular phones, hand held portables, and high density PC boards.

Features

- 250 mW Rating on FR-4 or FR-5 Board
- Zener Breakdown Voltage Range – 2.4 V to 75 V
- Package Designed for Optimal Automated Board Assembly
- Small Package Size for High Density Applications
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- Tight Tolerance Series Available (See Page 4)
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

Mechanical Characteristics

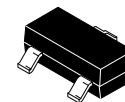
CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily Solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:
260°C for 10 Seconds

POLARITY: Cathode indicated by polarity band

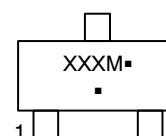
FLAMMABILITY RATING: UL 94 V-0



SOT-23
CASE 318
STYLE 8



MARKING DIAGRAM



XXX = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

| Device | Package | Shipping† |
|-----------------|---------------------|-------------------------|
| BZX84CxxxLT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| SZBZX84CxxxLT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| BZX84CxxxLT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |
| SZBZX84CxxxLT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |
| BZX84BxxxLT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| SZBZX84BxxxLT1G | SOT-23 (Pb-Free) | 3,000 / Tape & Reel |
| BZX84BxxxLT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |
| SZBZX84BxxxLT3G | SOT-23 (Pb-Free) | 10,000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

DEVICE MARKING INFORMATION

See specific marking information in the device marking column of the Electrical Characteristics table on page 3 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series

MAXIMUM RATINGS

| Rating | Symbol | Max | Unit |
|--|-----------------|-------------|----------------------------|
| Total Power Dissipation on FR-5 Board, (Note 1) @ $T_A = 25^\circ\text{C}$ Derated above 25°C | P_D | 250 | mW |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 2.0 | $\text{mW}/^\circ\text{C}$ |
| | | 500 | $^\circ\text{C}/\text{W}$ |
| Total Power Dissipation on Alumina Substrate, (Note 2) @ $T_A = 25^\circ\text{C}$ Derated above 25°C | P_D | 300 | mW |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 2.4 | $\text{mW}/^\circ\text{C}$ |
| | | 417 | $^\circ\text{C}/\text{W}$ |
| Junction and Storage Temperature Range | T_J, T_{stg} | -65 to +150 | $^\circ\text{C}$ |

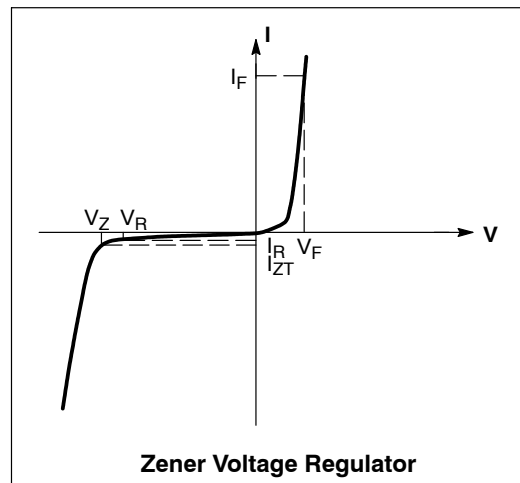
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- FR-5 = 1.0 X 0.75 X 0.62 in.
- Alumina = 0.4 X 0.3 X 0.024 in., 99.5% alumina.

ELECTRICAL CHARACTERISTICS

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 0.90\text{ V Max. @ } I_F = 10\text{ mA}$)

| Symbol | Parameter |
|--------------|---|
| V_Z | Reverse Zener Voltage @ I_{ZT} |
| I_{ZT} | Reverse Current |
| Z_{ZT} | Maximum Zener Impedance @ I_{ZT} |
| I_R | Reverse Leakage Current @ V_R |
| V_R | Reverse Voltage |
| I_F | Forward Current |
| V_F | Forward Voltage @ I_F |
| ΘV_Z | Maximum Temperature Coefficient of V_Z |
| C | Max. Capacitance @ $V_R = 0$ and $f = 1\text{ MHz}$ |



BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series

ELECTRICAL CHARACTERISTICS – BZX84CxxxLT1 SERIES (STANDARD TOLERANCE)

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) (T_A = 25°C unless otherwise noted, V_F = 0.90 V Max. @ I_F = 10 mA)
 (Devices listed in **bold, italic** are onsemi Preferred devices.)

| Device* | Device Marking | V _{Z1} (Volts) @ I _{ZT1} = 5 mA (Note 3) | | | Z _{ZT1} (Ω) @ I _{ZT1} = 5 mA | V _{Z2} (V) @ I _{ZT2} = 1 mA (Note 3) | | Z _{ZT2} (Ω) @ I _{ZT2} = 1 mA | V _{Z3} (V) @ I _{ZT3} = 20 mA (Note 3) | | Z _{ZT3} (Ω) @ I _{ZT3} = 20 mA | Max Reverse Leakage Current | | θ _{VZ} (mV/k) @ I _{ZT1} = 5 mA | | C (pF) @ V _R = 0 f = 1 MHz |
|-------------------------|----------------|--|------------|-------------|---|--|-------------|---|---|-------------|--|-----------------------------|------------------------|---|-------------|---|
| | | Min | Nom | Max | | Min | Max | | Min | Max | | I _R (μA) | V _R (Volts) | Min | Max | |
| | | Min | Nom | Max | Min | Max | Min | Max | Min | Max | I _R (μA) | V _R (Volts) | Min | Max | | |
| BZX84C2V4LT1G | Z11 | 2.2 | 2.4 | 2.6 | 100 | 1.7 | 2.1 | 600 | 2.6 | 3.2 | 50 | 50 | 1 | -3.5 | 0 | 450 |
| BZX84C2V7LT1G | Z12 | 2.5 | 2.7 | 2.9 | 100 | 1.9 | 2.4 | 600 | 3 | 3.6 | 50 | 20 | 1 | -3.5 | 0 | 450 |
| BZX84C3V0LT1G | Z13 | 2.8 | 3 | 3.2 | 95 | 2.1 | 2.7 | 600 | 3.3 | 3.9 | 50 | 10 | 1 | -3.5 | 0 | 450 |
| BZX84C3V3LT1G | Z14 | 3.1 | 3.3 | 3.5 | 95 | 2.3 | 2.9 | 600 | 3.6 | 4.2 | 40 | 5 | 1 | -3.5 | 0 | 450 |
| BZX84C3V6LT1G | Z15 | 3.4 | 3.6 | 3.8 | 90 | 2.7 | 3.3 | 600 | 3.9 | 4.5 | 40 | 5 | 1 | -3.5 | 0 | 450 |
| BZX84C3V9LT1G | Z16 | 3.7 | 3.9 | 4.1 | 90 | 2.9 | 3.5 | 600 | 4.1 | 4.7 | 30 | 3 | 1 | -3.5 | -2.5 | 450 |
| BZX84C4V3LT1G | W9 | 4 | 4.3 | 4.6 | 90 | 3.3 | 4 | 600 | 4.4 | 5.1 | 30 | 3 | 1 | -3.5 | 0 | 450 |
| BZX84C4V7LT1/T3G | Z1 | 4.4 | 4.7 | 5 | 80 | 3.7 | 4.7 | 500 | 4.5 | 5.4 | 15 | 3 | 2 | -3.5 | 0.2 | 260 |
| BZX84C5V1LT1/T3G | Z2 | 4.8 | 5.1 | 5.4 | 60 | 4.2 | 5.3 | 480 | 5 | 5.9 | 15 | 2 | 2 | -2.7 | 1.2 | 225 |
| BZX84C5V6LT1/T3G | Z3 | 5.2 | 5.6 | 6 | 40 | 4.8 | 6 | 400 | 5.2 | 6.3 | 10 | 1 | 2 | -2.0 | 2.5 | 200 |
| BZX84C6V2LT1/T3G | Z4 | 5.8 | 6.2 | 6.6 | 10 | 5.6 | 6.6 | 150 | 5.8 | 6.8 | 6 | 3 | 4 | 0.4 | 3.7 | 185 |
| BZX84C6V8LT1/T3G | Z5 | 6.4 | 6.8 | 7.2 | 15 | 6.3 | 7.2 | 80 | 6.4 | 7.4 | 6 | 2 | 4 | 1.2 | 4.5 | 155 |
| BZX84C7V5LT1G | Z6 | 7 | 7.5 | 7.9 | 15 | 6.9 | 7.9 | 80 | 7 | 8 | 6 | 1 | 5 | 2.5 | 5.3 | 140 |
| BZX84C8V2LT1G | Z7 | 7.7 | 8.2 | 8.7 | 15 | 7.6 | 8.7 | 80 | 7.7 | 8.8 | 6 | 0.7 | 5 | 3.2 | 6.2 | 135 |
| BZX84C9V1LT1/T3G | Z8 | 8.5 | 9.1 | 9.6 | 15 | 8.4 | 9.6 | 100 | 8.5 | 9.7 | 8 | 0.5 | 6 | 3.8 | 7.0 | 130 |
| BZX84C10LT1G | Z9 | 9.4 | 10 | 10.6 | 20 | 9.3 | 10.6 | 150 | 9.4 | 10.7 | 10 | 0.2 | 7 | 4.5 | 8.0 | 130 |
| BZX84C11LT1G | Y1 | 10.4 | 11 | 11.6 | 20 | 10.2 | 11.6 | 150 | 10.4 | 11.8 | 10 | 0.1 | 8 | 5.4 | 9.0 | 130 |
| BZX84C12LT1G | Y2 | 11.4 | 12 | 12.7 | 25 | 11.2 | 12.7 | 150 | 11.4 | 12.9 | 10 | 0.1 | 8 | 6.0 | 10.0 | 130 |
| BZX84C13LT1G | Y3 | 12.4 | 13 | 14.1 | 30 | 12.3 | 14 | 170 | 12.5 | 14.2 | 15 | 0.1 | 8 | 7.0 | 11.0 | 120 |
| BZX84C15LT1/T3G | Y4 | 13.8 | 15 | 15.6 | 30 | 13.7 | 15.5 | 200 | 13.9 | 15.7 | 20 | 0.05 | 10.5 | 9.2 | 13.0 | 110 |
| BZX84C16LT1G | Y5 | 15.3 | 16 | 17.1 | 40 | 15.2 | 17 | 200 | 15.4 | 17.2 | 20 | 0.05 | 11.2 | 10.4 | 14.0 | 105 |
| BZX84C18LT1/T3G | Y6 | 16.8 | 18 | 19.1 | 45 | 16.7 | 19 | 225 | 16.9 | 19.2 | 20 | 0.05 | 12.6 | 12.4 | 16.0 | 100 |
| BZX84C20LT1G | Y7 | 18.8 | 20 | 21.2 | 55 | 18.7 | 21.1 | 225 | 18.9 | 21.4 | 20 | 0.05 | 14 | 14.4 | 18.0 | 85 |
| BZX84C22LT1G | Y8 | 20.8 | 22 | 23.3 | 55 | 20.7 | 23.2 | 250 | 20.9 | 23.4 | 25 | 0.05 | 15.4 | 16.4 | 20.0 | 85 |
| BZX84C24LT1G | Y9 | 22.8 | 24 | 25.6 | 70 | 22.7 | 25.5 | 250 | 22.9 | 25.7 | 25 | 0.05 | 16.8 | 18.4 | 22.0 | 80 |
| Device* | Device Marking | V _{Z1} Below @ I _{ZT1} = 2 mA | | | Z _{ZT1} Below @ I _{ZT1} = 2 mA | V _{Z2} Below @ I _{ZT2} = 0.1 mA | | Z _{ZT2} Below @ I _{ZT2} = 0.5 mA | V _{Z3} Below @ I _{ZT3} = 10 mA | | Z _{ZT3} Below @ I _{ZT3} = 10 mA | Max Reverse Leakage Current | | θ _{VZ} (mV/k) Below @ I _{ZT1} = 2 mA | | C (pF) @ V _R = 0 f = 1 MHz |
| | | Min | Nom | Max | | Min | Max | | Min | Max | | I _R (μA) | V _R (V) | Min | Max | |
| | | Min | Nom | Max | Min | Max | Min | Max | Min | Max | I _R (μA) | V _R (V) | Min | Max | | |
| BZX84C27LT1G | Y10 | 25.1 | 27 | 28.9 | 80 | 25 | 28.9 | 300 | 25.2 | 29.3 | 45 | 0.05 | 18.9 | 21.4 | 25.3 | 70 |
| BZX84C30LT1G | Y11 | 28 | 30 | 32 | 80 | 27.8 | 32 | 300 | 28.1 | 32.4 | 50 | 0.05 | 21 | 24.4 | 29.4 | 70 |
| BZX84C33LT1/T3G | Y12 | 31 | 33 | 35 | 80 | 30.8 | 35 | 325 | 31.1 | 35.4 | 55 | 0.05 | 23.1 | 27.4 | 33.4 | 70 |
| BZX84C36LT1G | Y13 | 34 | 36 | 38 | 90 | 33.8 | 38 | 350 | 34.1 | 38.4 | 60 | 0.05 | 25.2 | 30.4 | 37.4 | 70 |
| BZX84C39LT1G | Y14 | 37 | 39 | 41 | 130 | 36.7 | 41 | 350 | 37.1 | 41.5 | 70 | 0.05 | 27.3 | 33.4 | 41.2 | 45 |
| BZX84C43LT1G | Y15 | 40 | 43 | 46 | 150 | 39.7 | 46 | 375 | 40.1 | 46.5 | 80 | 0.05 | 30.1 | 37.6 | 46.6 | 40 |
| BZX84C47LT1G | Y16 | 44 | 47 | 50 | 170 | 43.7 | 50 | 375 | 44.1 | 50.5 | 90 | 0.05 | 32.9 | 42.0 | 51.8 | 40 |
| BZX84C51LT1G | Y17 | 48 | 51 | 54 | 180 | 47.6 | 54 | 400 | 48.1 | 54.6 | 100 | 0.05 | 35.7 | 46.6 | 57.2 | 40 |
| BZX84C56LT1G | Y18 | 52 | 56 | 60 | 200 | 51.5 | 60 | 425 | 52.1 | 60.8 | 110 | 0.05 | 39.2 | 52.2 | 63.8 | 40 |
| BZX84C62LT1G | Y19 | 58 | 62 | 66 | 215 | 57.4 | 66 | 450 | 58.2 | 67 | 120 | 0.05 | 43.4 | 58.8 | 71.6 | 35 |
| BZX84C68LT1G | Y20 | 64 | 68 | 72 | 240 | 63.4 | 72 | 475 | 64.2 | 73.2 | 130 | 0.05 | 47.6 | 65.6 | 79.8 | 35 |
| BZX84C75LT1G | Y21 | 70 | 75 | 79 | 255 | 69.4 | 79 | 500 | 70.3 | 80.2 | 140 | 0.05 | 52.5 | 73.4 | 88.6 | 35 |

3. Zener voltage is measured with a pulse test current I_Z at an ambient temperature of 25°C.

*Includes SZ-prefix devices where applicable.

BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series

ELECTRICAL CHARACTERISTICS – BZX84BxxxL (Tight Tolerance Series)

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 0.90\text{ V Max. @ } I_F = 10\text{ mA}$)

| Device | Device Marking | V_Z (Volts) @ $I_{ZT} = 5\text{ mA}$ (Note 4) | | | $Z_{ZT} (\Omega)$ @ $I_{ZT} = 5\text{ mA}$ (Note 4) | Max Reverse Leakage Current | | θ_{VZ} (mV/k) @ $I_{ZT} = 5\text{ mA}$ | | C (pF) @ $V_R = 0$, f = 1 MHz |
|--------------------|----------------|--|-----|------|---|-----------------------------|---------|---|-----|--------------------------------------|
| | | | | | | I_R | V_R | | | |
| | | Min | Nom | Max | Max | μA | @ Volts | Min | Max | |
| BZX84B3V3LT1G | T2A | 3.23 | 3.3 | 3.37 | 95 | 5 | 1 | -3.5 | 0 | 450 |
| BZX84B4V7LT1G | T10 | 4.61 | 4.7 | 4.79 | 80 | 3 | 2 | -3.5 | 0.2 | 260 |
| BZX84B5V1LT1G | T11 | 5.00 | 5.1 | 5.20 | 60 | 2 | 2 | -2.7 | 1.2 | 225 |
| BZX84B5V6LT1G | T12 | 5.49 | 5.6 | 5.71 | 40 | 1 | 2 | -2 | 2.5 | 200 |
| BZX84B6V2LT1G | T13 | 6.08 | 6.2 | 6.32 | 10 | 3 | 4 | 0.4 | 3.7 | 185 |
| BZX84B6V8LT1G | T14 | 6.66 | 6.8 | 6.94 | 15 | 2 | 4 | 1.2 | 4.5 | 155 |
| BZX84B7V5LT1G | T15 | 7.35 | 7.5 | 7.65 | 15 | 1 | 5 | 2.5 | 5.3 | 140 |
| BZX84B8V2LT1G | T16 | 8.04 | 8.2 | 8.36 | 15 | 0.7 | 5 | 3.2 | 6.2 | 135 |
| BZX84B9V1LT1G, T3G | T17 | 8.92 | 9.1 | 9.28 | 15 | 0.5 | 6 | 3.8 | 7 | 130 |
| BZX84B10LT1G | T2E | 9.8 | 10 | 10.2 | 20 | 0.2 | 7 | 4.5 | 8 | 130 |
| BZX84B12LT1G | T18 | 11.8 | 12 | 12.2 | 25 | 0.1 | 8 | 6 | 10 | 130 |
| BZX84B15LT1G | T22 | 14.7 | 15 | 15.3 | 30 | 0.05 | 10.5 | 9.2 | 13 | 110 |
| BZX84B16LT1G | T19 | 15.7 | 16 | 16.3 | 40 | 0.05 | 11.2 | 10.4 | 14 | 105 |
| BZX84B18LT1G | T20 | 17.6 | 18 | 18.4 | 45 | 0.05 | 12.6 | 12.4 | 16 | 100 |
| BZX84B22LT1G | T24 | 21.6 | 22 | 22.4 | 55 | 0.05 | 15.4 | 16.4 | 20 | 85 |
| BZX84B24LT1G | T25 | 23.5 | 24 | 24.5 | 70 | 0.05 | 16.8 | 18.4 | 22 | 80 |

4. Zener voltage is measured with a pulse test current I_Z at an ambient temperature of 25°C .

ELECTRICAL CHARACTERISTICS – BZX84BxxxL (Tight Tolerance Series)

(Pinout: 1-Anode, 2-No Connection, 3-Cathode) ($T_A = 25^\circ\text{C}$ unless otherwise noted, $V_F = 0.90\text{ V Max. @ } I_F = 10\text{ mA}$)

| Device* | Device Marking | V_Z (Volts) @ $I_{ZT} = 2\text{ mA}$ (Note 4) | | | $Z_{ZT} (\Omega)$ @ $I_{ZT} = 2\text{ mA}$ (Note 4) | Max Reverse Leakage Current | | θ_{VZ} (mV/k) @ $I_{ZT} = 2\text{ mA}$ | | C (pF) @ $V_R = 0$, f = 1 MHz |
|--------------|----------------|--|-----|------|---|-----------------------------|---------|---|------|--------------------------------------|
| | | | | | | I_R | V_R | | | |
| | | Min | Nom | Max | Max | μA | @ Volts | Min | Max | |
| BZX84B27LT1G | T27 | 26.5 | 27 | 27.5 | 80 | 0.05 | 18.9 | 21.4 | 25.3 | 70 |

*Includes SZ-prefix devices where applicable.

BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series

TYPICAL CHARACTERISTICS

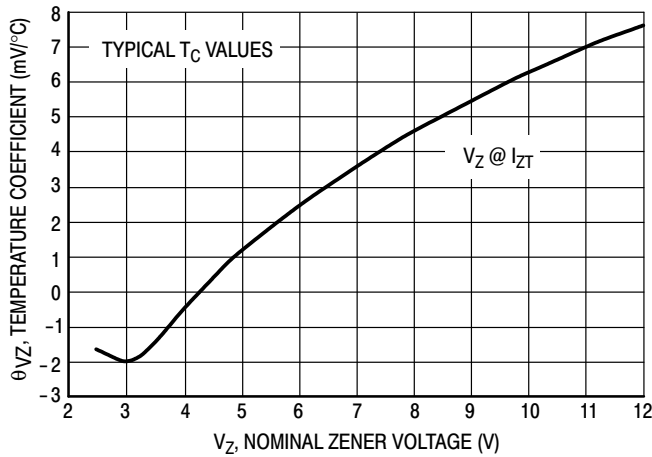


Figure 1. Temperature Coefficients
(Temperature Range -55°C to +150°C)

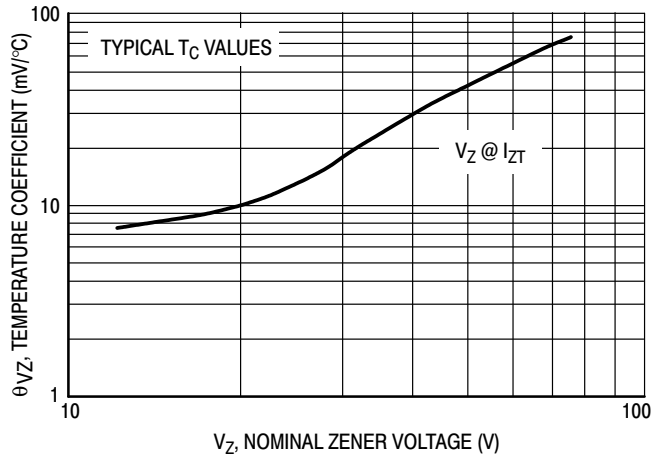


Figure 2. Temperature Coefficients
(Temperature Range -55°C to +150°C)

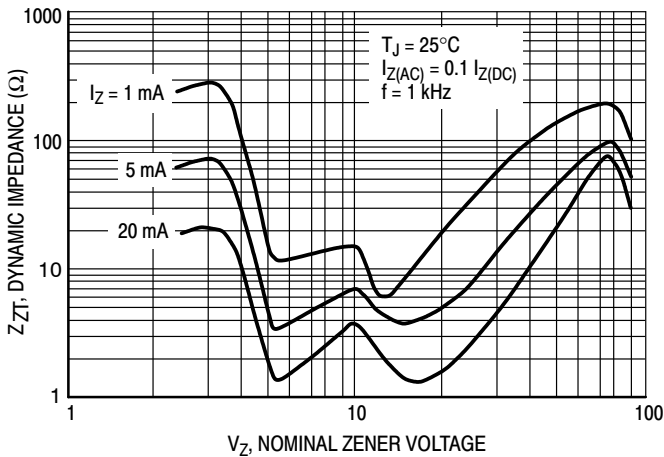


Figure 3. Effect of Zener Voltage on Zener Impedance

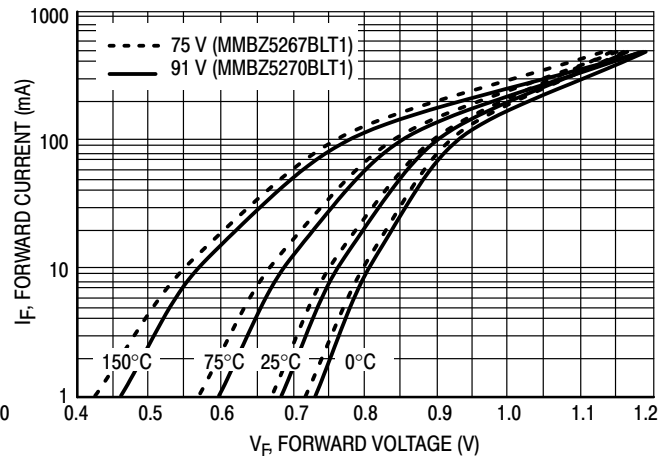


Figure 4. Typical Forward Voltage

BZX84BxxxLT1G, BZX84CxxxLT1G Series, SZBZX84BxxxLT1G, SZBZX84CxxxLT1G Series

TYPICAL CHARACTERISTICS

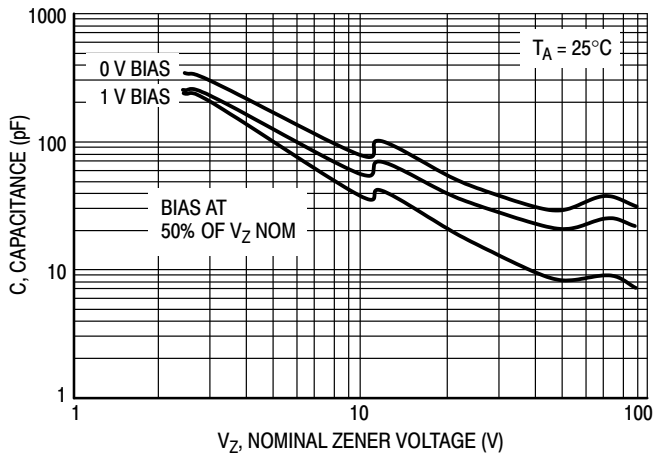


Figure 5. Typical Capacitance

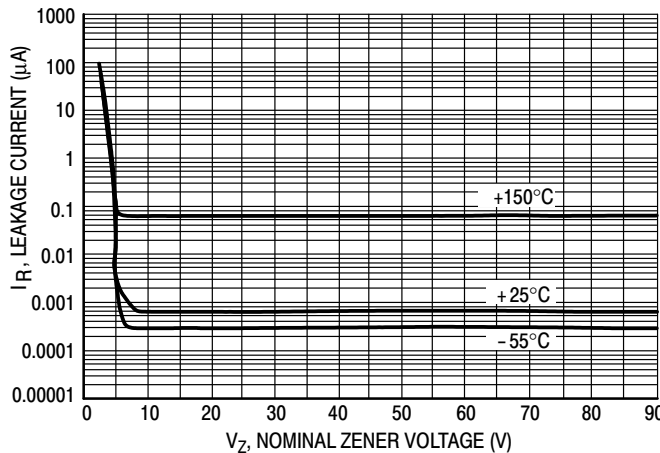


Figure 6. Typical Leakage Current

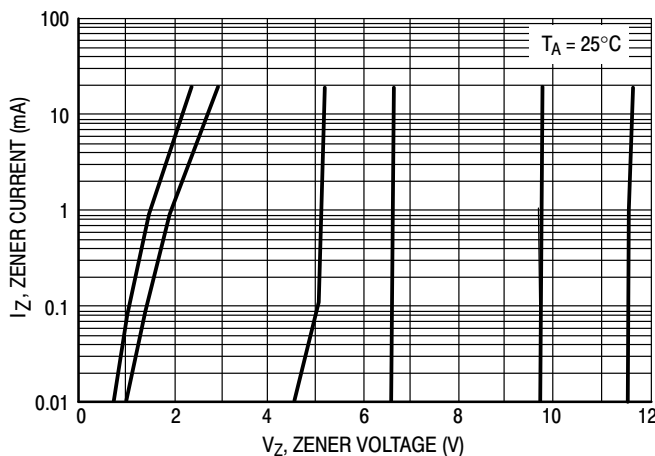


Figure 7. Zener Voltage versus Zener Current (V_Z Up to 12 V)

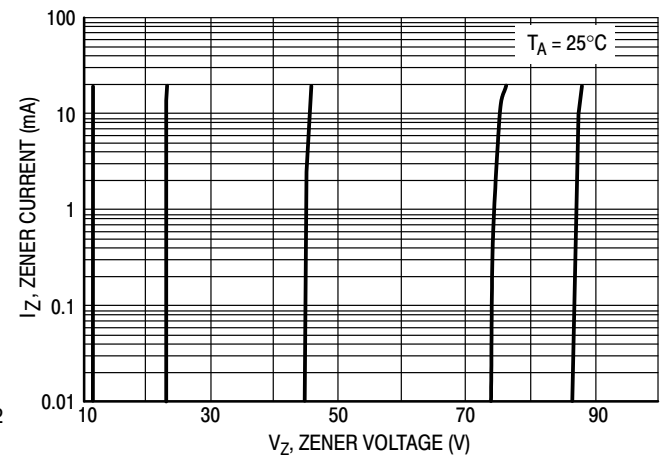
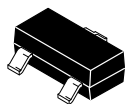


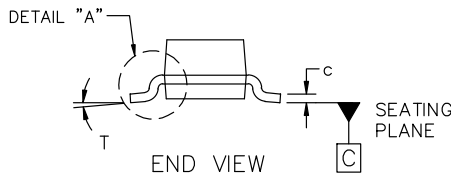
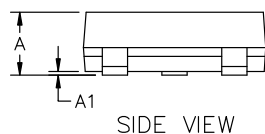
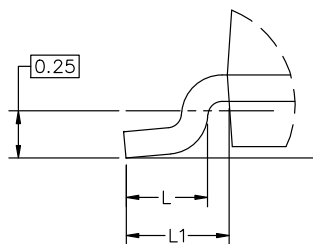
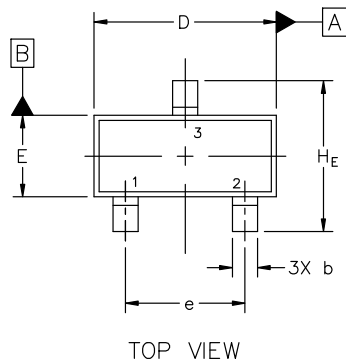
Figure 8. Zener Voltage versus Zener Current (12 V to 91 V)



SCALE 4:1

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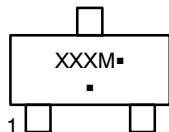
DATE 14 AUG 2024



| MILLIMETERS | | | |
|-------------|------|------|------|
| DIM | MIN | NOM | MAX |
| A | 0.89 | 1.00 | 1.11 |
| A1 | 0.01 | 0.06 | 0.10 |
| b | 0.37 | 0.44 | 0.50 |
| c | 0.08 | 0.14 | 0.20 |
| D | 2.80 | 2.90 | 3.04 |
| E | 1.20 | 1.30 | 1.40 |
| e | 1.78 | 1.90 | 2.04 |
| L | 0.30 | 0.43 | 0.55 |
| L1 | 0.35 | 0.54 | 0.69 |
| HE | 2.10 | 2.40 | 2.64 |
| T | 0° | --- | 10° |

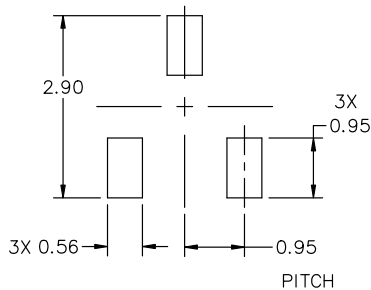
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
 2. CONTROLLING DIMENSIONS: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

| | | |
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STYLE 1 THRU 5:
 CANCELLED

STYLE 6:
 PIN 1. BASE
 2. EMITTER
 3. COLLECTOR

STYLE 7:
 PIN 1. EMITTER
 2. BASE
 3. COLLECTOR

STYLE 8:
 PIN 1. ANODE
 2. NO CONNECTION
 3. CATHODE

STYLE 9:
 PIN 1. ANODE
 2. ANODE
 3. CATHODE

STYLE 10:
 PIN 1. DRAIN
 2. SOURCE
 3. GATE

STYLE 11:
 PIN 1. ANODE
 2. CATHODE
 3. CATHODE-ANODE

STYLE 12:
 PIN 1. CATHODE
 2. CATHODE
 3. ANODE

STYLE 13:
 PIN 1. SOURCE
 2. DRAIN
 3. GATE

STYLE 14:
 PIN 1. CATHODE
 2. GATE
 3. ANODE

STYLE 15:
 PIN 1. GATE
 2. CATHODE
 3. ANODE

STYLE 16:
 PIN 1. ANODE
 2. CATHODE
 3. CATHODE

STYLE 17:
 PIN 1. NO CONNECTION
 2. ANODE
 3. CATHODE

STYLE 18:
 PIN 1. NO CONNECTION
 2. CATHODE
 3. ANODE

STYLE 19:
 PIN 1. CATHODE
 2. ANODE
 3. CATHODE-ANODE

STYLE 20:
 PIN 1. CATHODE
 2. ANODE
 3. GATE

STYLE 21:
 PIN 1. GATE
 2. SOURCE
 3. DRAIN

STYLE 22:
 PIN 1. RETURN
 2. OUTPUT
 3. INPUT

STYLE 23:
 PIN 1. ANODE
 2. ANODE
 3. CATHODE

STYLE 24:
 PIN 1. GATE
 2. DRAIN
 3. SOURCE

STYLE 25:
 PIN 1. ANODE
 2. CATHODE
 3. GATE

STYLE 26:
 PIN 1. CATHODE
 2. ANODE
 3. NO CONNECTION

STYLE 27:
 PIN 1. CATHODE
 2. CATHODE
 3. CATHODE

STYLE 28:
 PIN 1. ANODE
 2. ANODE
 3. ANODE

| | | |
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